JJMICROELECTRONICS

100V, 191A, 2.5mΩ N-channel Power SGT MOSFET

JMSH1003VE

Features

- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS Tested
- 100% ΔVds Tested
- Halogen-free; RoHS-compliant

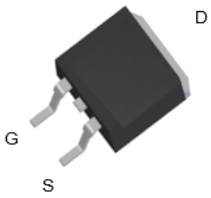
Applications

- Load Switch
- PWM Application
- Power Management

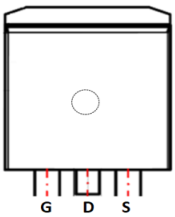
Product Summary

Parameters	Value	Unit
V_{DSS}	100	V
$V_{GS(th)\_Typ}$	3.0	V
I_D(@V_{GS}=10V)	191	A
$R_{DS(ON)\_Typ}$(@V_{GS}=10V	2.5	mΩ

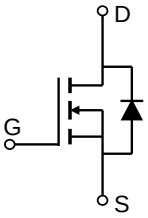
RoHS



TO-263-3LTop View



Pin Assignment



Schematic Diagram

Ordering Information

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
JMSH1003VE-13	SH1003V	3	Tape&Reel	TO-263-3L	800	4000

Absolute Maximum Ratings (@ T_C = 25°C unless otherwise specified)

Symbol	Parameter		Value	Unit
V_{DS}	Drain-to-Source Voltage		100	V
V_{GS}	Gate-to-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C = 25°C	191	A
		T_C = 100°C	121	
I_{DM}	Pulsed Drain Current (1)		Refer to Fig.4	A
E_{AS}	Single Pulsed Avalanche Energy (2)		1118	mJ
P_D	Power Dissipation	T_C = 25°C	213	W
		T_C = 100°C	85	
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient(3)	34	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.6	

Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	100	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 80V, V_{GS} = 0V	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	2.1	3.0	3.9	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance(4)	V_{GS} = 10V, I_D = 20A	-	2.5	3.3	mΩ
Dynamic Characteristics						
R_g	Gate Resistance	f = 1MHz	-	1.2	-	Ω
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 50V, f = 1MHz	6105	8547	12821	pF
C_{oss}	Output Capacitance		843	1180	1770	pF
C_{rss}	Reverse Transfer Capacitance		22	31	62	pF
Q_g	Total Gate Charge	V_{GS} = 0 to 10V V_{DS} = 50V, I_D = 20A	88	123	185	nC
Q_{gs}	Gate Source Charge		30	42	63	nC
Q_{gd}	Gate Drain("Miller") Charge		18	25	38	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	V_{GS} = 10V, V_{DD} = 50V I_D= 20A, R_{GEN} = 3Ω	-	30	-	ns
t_r	Turn-On Rise Time		-	35	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	66	-	ns
t_f	Turn-Off Fall Time		-	28	-	ns
Body Diode Characteristics						
I_S	Maximum Continuous Body Diode Forward Current		-	-	191	A
I_{SM}	Maximum Pulsed Body Diode Forward Current		-	-	764	A
V_{SD}	Body Diode Forward Voltage	V_{GS} = 0V, I_S = 20A	-		1.2	V
trr	Body Diode Reverse Recovery Time	I_F = 20A, di/dt = 100A/us	61	86	128	ns
Qrr	Body Diode Reverse Recovery Charge		-	230	-	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2. E_{AS} condition: Starting T_J=25C, V_{DD}=50V, V_{GS}=10V, R_G=25ohm, L=3mH, I_{AS}=27.3A, V_{DD}=0V during time in avalanche.
3. $R_{\theta JA}$ is measured with the device mounted on a 1inch^2 pad of 2oz copper FR4 PCB.
4. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%.

Typical Performance Characteristics

Figure 1: Power De-rating

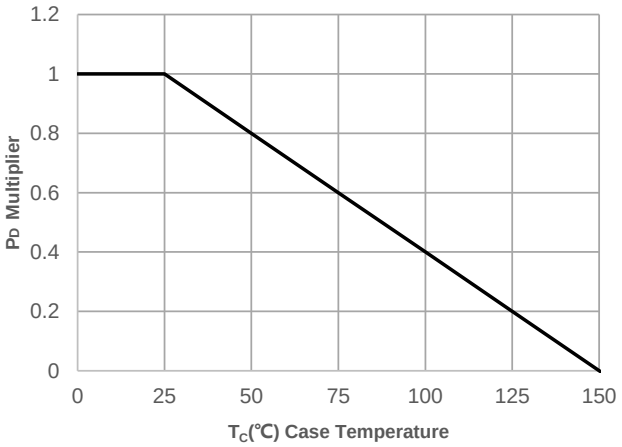


Figure 2: Current De-rating

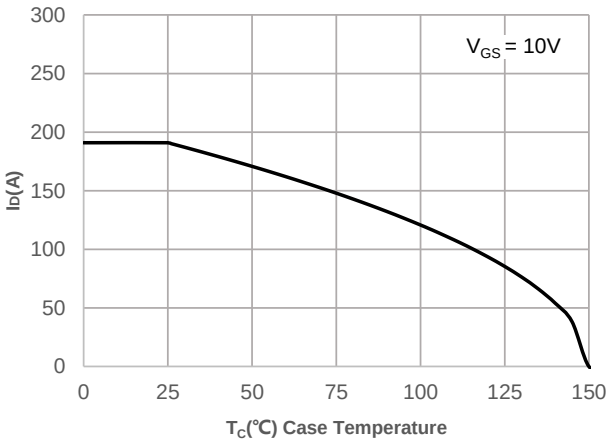


Figure 3: Normalized Maximum Transient Thermal Impedance

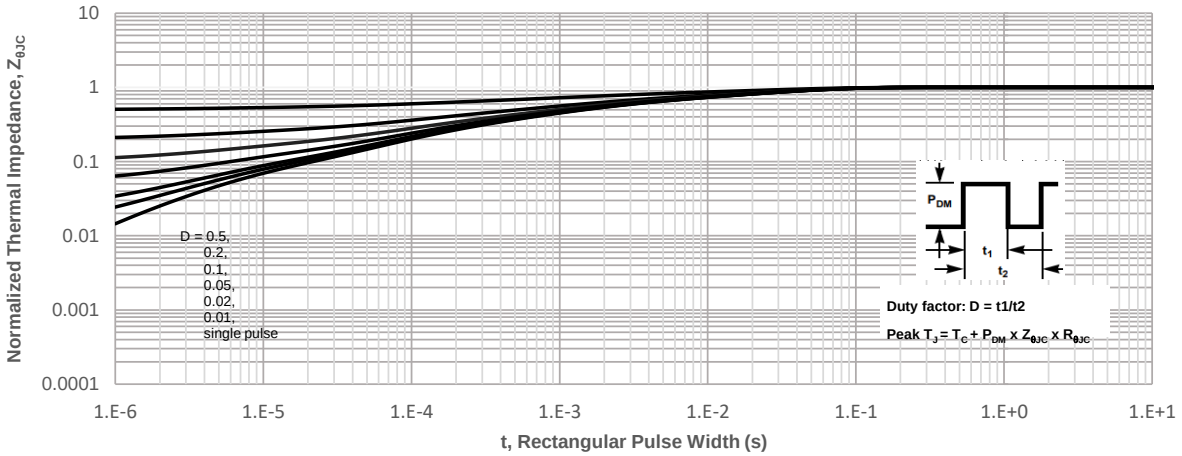
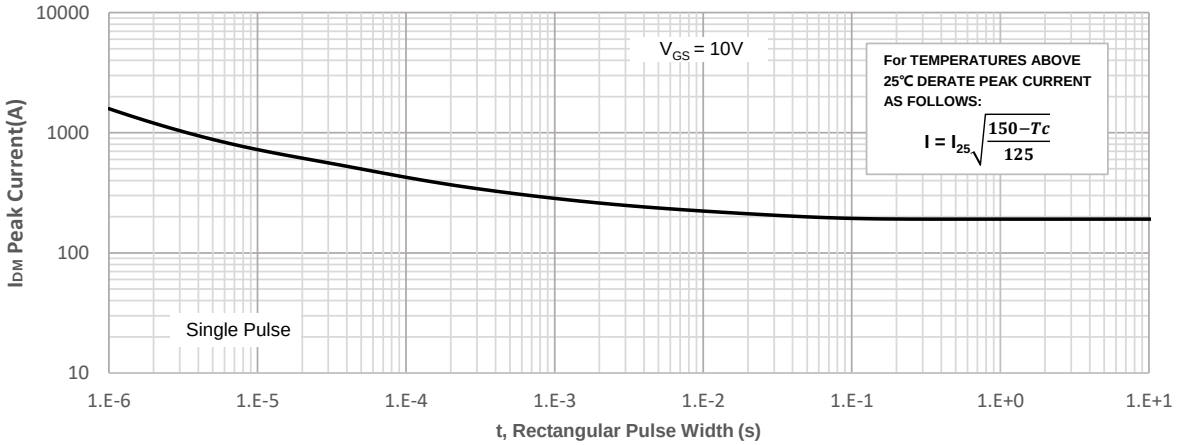


Figure 4: Peak Current Capacity



Typical Performance Characteristics

Figure 5: Output Characteristics

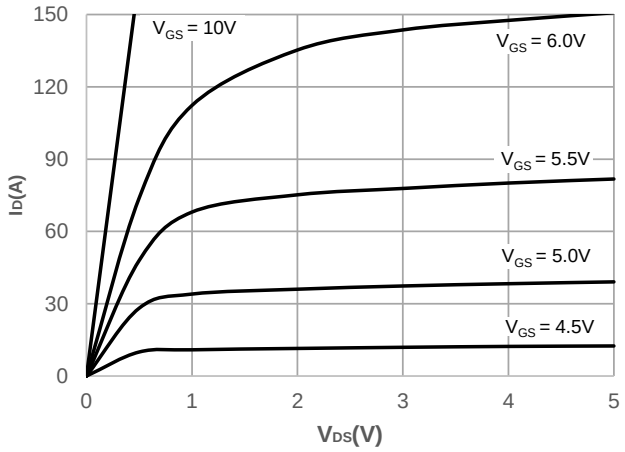


Figure 6: Typical Transfer Characteristics

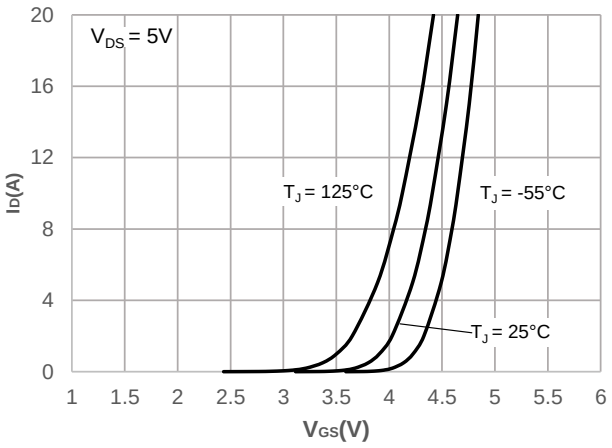


Figure 7: On-resistance vs. Drain Current

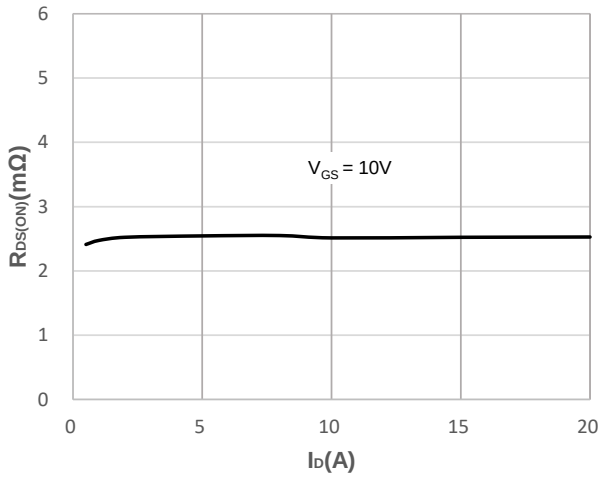


Figure 8: Body Diode Characteristics

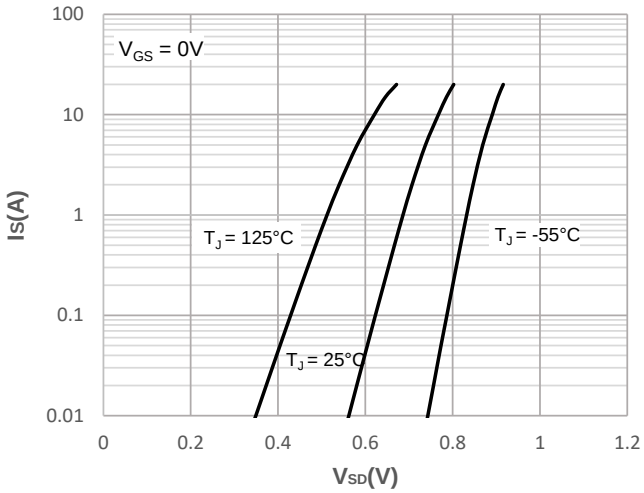


Figure 9: Gate Charge Characteristics

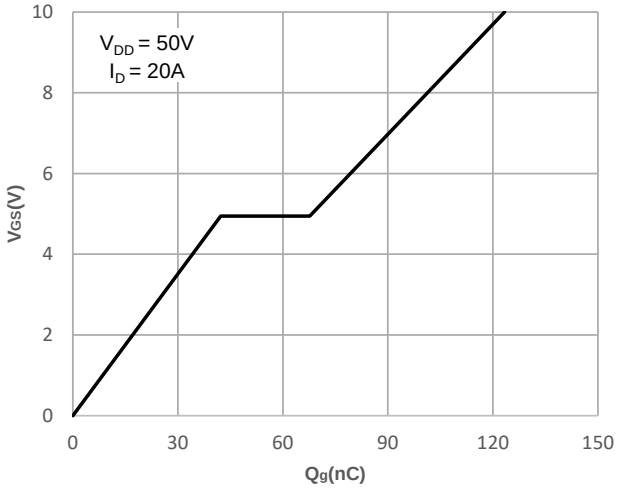
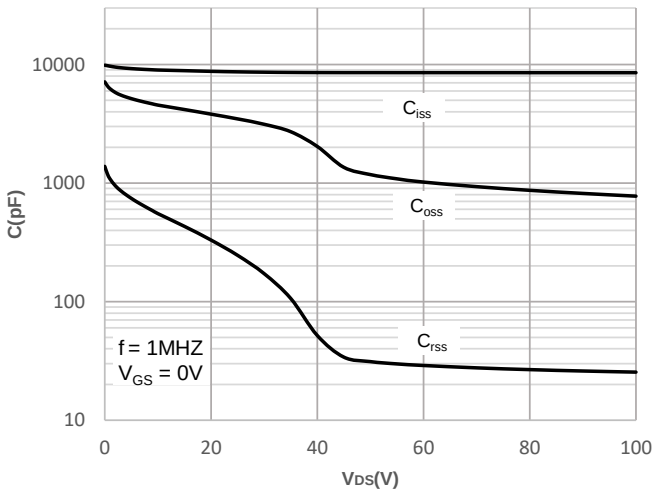


Figure 10: Capacitance Characteristics



Typical Performance Characteristics

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

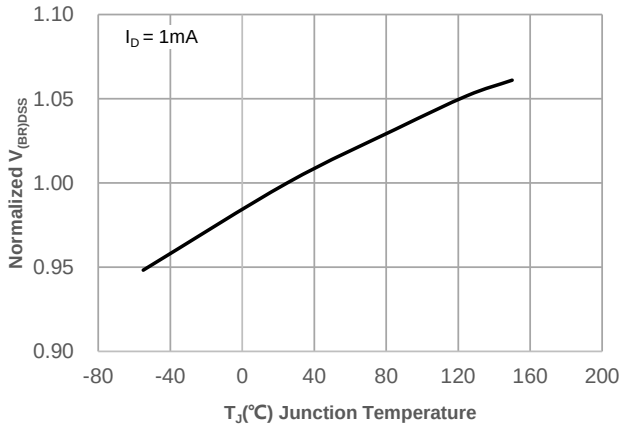


Figure 12: Normalized on Resistance vs. Junction Temperature

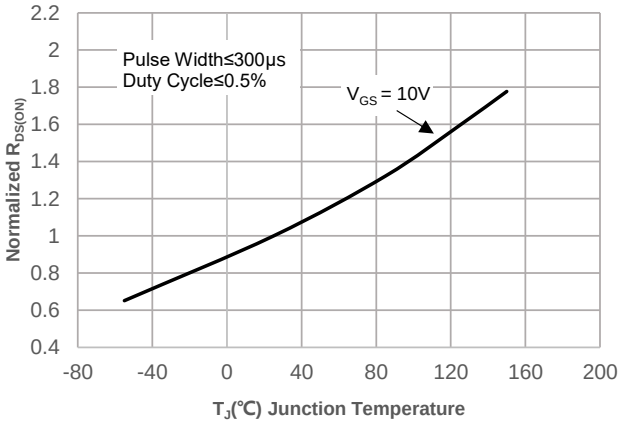


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

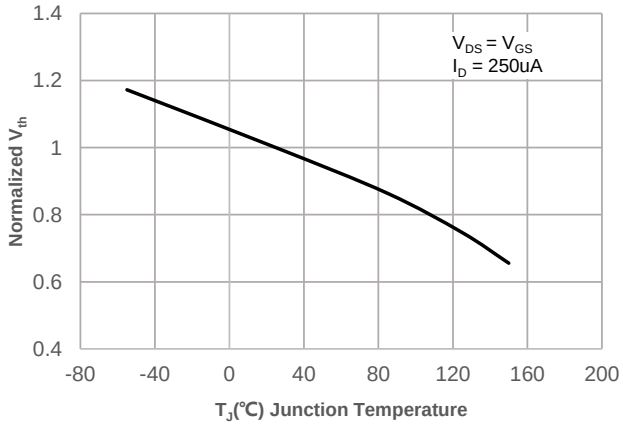


Figure 14: $R_{DS(ON)}$ vs. V_{GS}

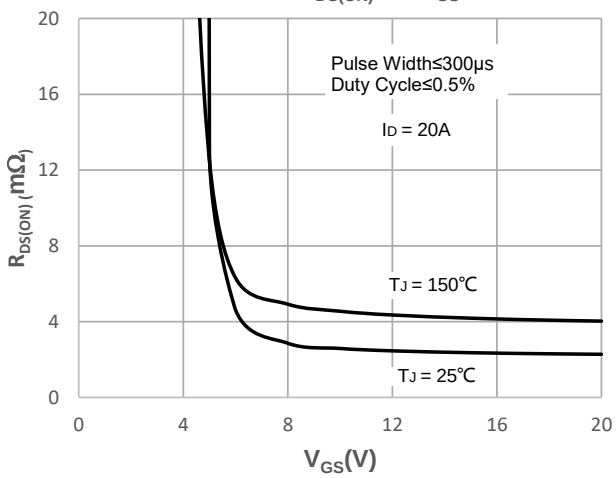
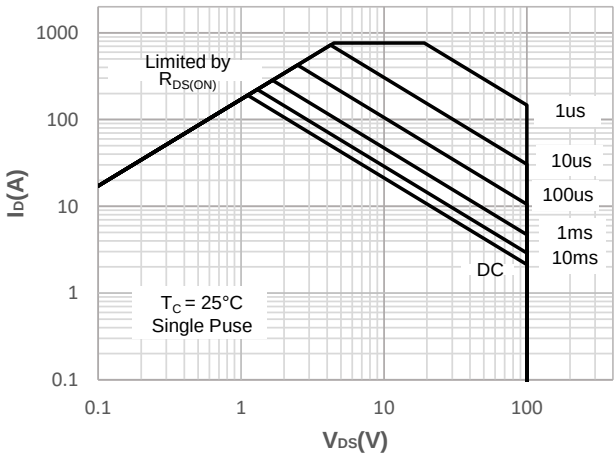


Figure 15: Maximum Safe Operating Area



Test Circuit

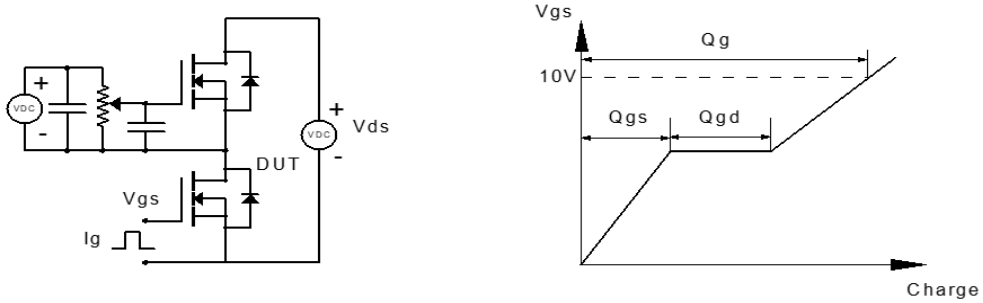


Figure 1: Gate Charge Test Circuit & Waveform

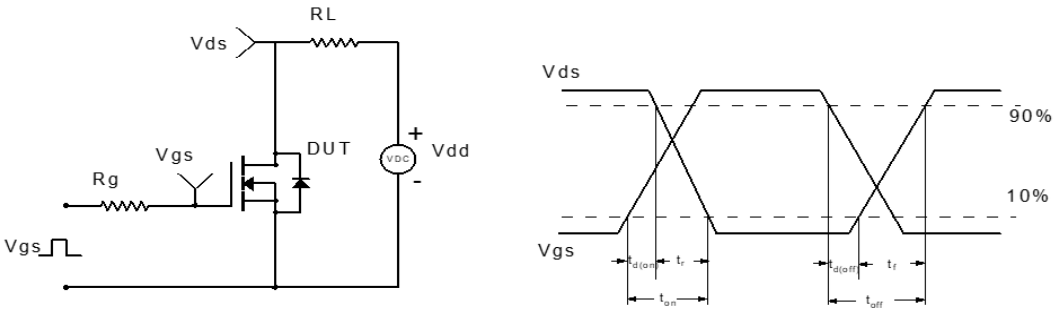


Figure 2: Resistive Switching Test Circuit & Waveform

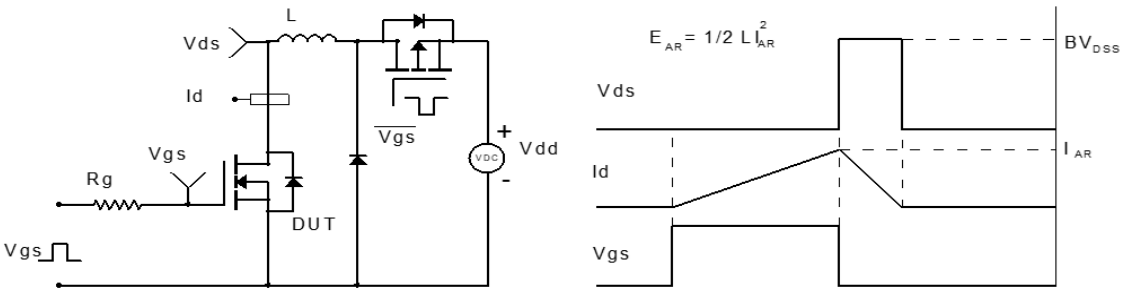


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

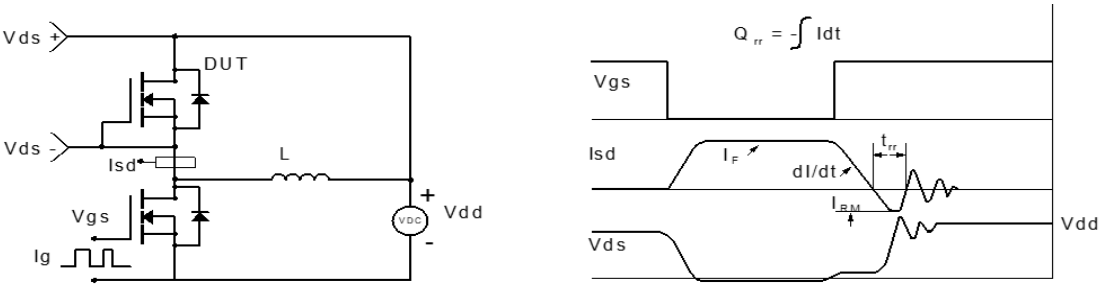
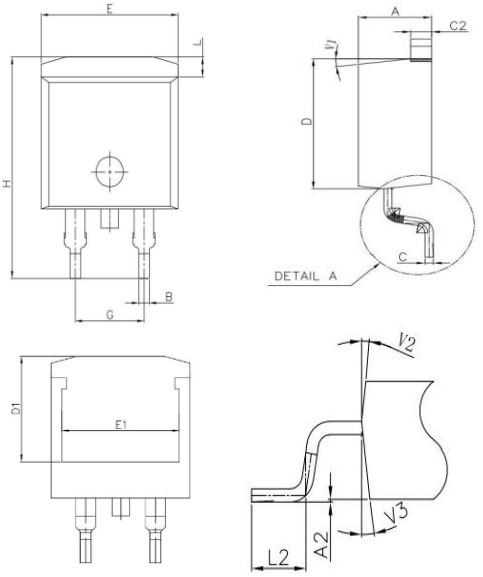


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(TO-263 -3L)

Package Outline



SYMBOL	DIMENSIONS		
	MIN	NOM	MAX
A	4.3	4.55	4.7
A2	0		0.15
B	0.75	0.8	0.85
C	0.38	0.46	0.55
C2	1.25	1.3	1.35
D	8.9	9.3	9.6
D1	7.4	7.65	7.9
E	9.9	10.05	10.21
E1	8.3	8.6	8.9
G	5.03	5.08	5.13
H	14.7	15	15.8
L2	2.2	2.35	2.5
L	1.16	1.36	1.61
V1	5°	7°	9°
V2	3°	5°	7°
V3	6°	8°	10°

Land Pattern
(Only for Reference)